

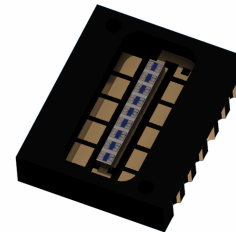
General Description

OIT26 consists in a silicon phototransistor's monolithic array.

The phototransistors have a common collector, every emitter is available as a pad. The pitch of the silicon arrays is 0.6 mm, while the component electrical pitch is 1.27 mm. The active area of each element is 0.2 x 0.45 mm. The encapsulant is an high quality microelectronic transparent resin, its transmission value is 100% in the range 300-900nm.

The advantages of this product are the high uniformity of the silicon sensors, due to the monolithic construction and the high optical responsivity, due to the antireflective coating deposited on the phototransistor's areas.

The packaging method is oriented to industrial harsh applications, which means high temperature range, high stability in time and very high uniformity of the silicon cells.



Features

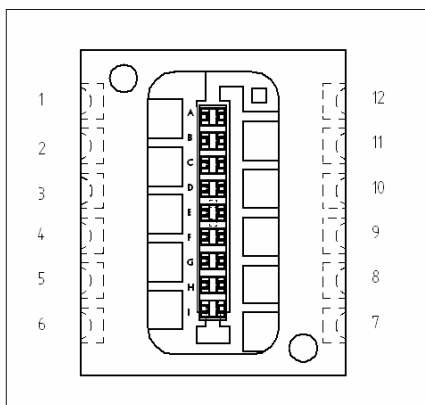
- High Gain Uniformity $\pm 10\%$
- High Reliability
- Optical Pitch = 0.6 mm
- Available in SMT Suitable Version
- RoHS compliant

Pin Functions

No.	Name	Function
1	N.C.	Not connected
2	AE	Phototransistor A Emitter
3	CE	Phototransistor C Emitter
4	EE	Phototransistor E Emitter
5	GE	Phototransistor G Emitter
6	IE	Phototransistor I Emitter
7	N.C.	Not connected
8	HE	Phototransistor H Emitter
9	FE	Phototransistor F Emitter
10	DE	Phototransistor D Emitter
11	BE	Phototransistor B Emitter
12	CC	Common Collector

Applications

Incremental encoders
 Optical receivers
 Optical encoders
 Controls/Drives
 General Purpose



TOP VIEW

Ordering Information

OIT26 Monolithic 9 Silicon NPN Phototransistor Array Chip with Active Area of Each Phototransistor 0.2 x 0.45 mm².

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Min	Max	Unit
T _A	Operating Temperature Range	-40	85	°C
T _S	Storage Temperature	-40	100	°C
T _{Sol}	Lead Temperature (solder) 3s		230	°C
V _{R(BR)}	Breakdown Voltage Collector-Emitter @ T _A =25°C I _B =100nA I _C =1mA	50		V
P _D	Power Dissipation @ T _A =25°C		150	mW

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _D	Dark Current	V _R =10V		10	100	nA
R _λ	Responsivity	V _{CE} =5V λ=880nm	0.5			A/W
λ _p	Peak Responsivity	V _{CE} =5V		750		nm
Δλ	Spectral Bandwidth @ 50%	V _{CE} =5V	500		950	nm
I _{ec0}	Emitter-Collector Current	V _{CE} =7.7V		0.1	100	μA
I _{ce0}	Collector-Emitter Current	V _{CE} =52V		0.1	100	μA
H _{FE}	Gain	V _{CC} =5V I _C =2mA		600		
V _{CE(sat)}	Saturation Voltage	I _E =2mA I _B =20μA		160	200	mV
I _{C(on)}	On-state Collector Current	V _{CE} =5V E _E =1.0mW/cm ²		1		mA

AC SWITCHING CHARACTERISTICS

T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _R	Rise Time	V _{CC} =5V I _C =1mA R ₁ =1kΩ		10		μs
t _F	Fall Time	V _{CC} =5V I _C =1mA R ₁ =1kΩ		11		μs

MECHANICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
A	Phototransistor Active Area			0.09		mm ²
L	Length of the Active Area			0.2		mm
W	Width of the Active Area			0.45		mm

MECHANICAL DIMENSIONS

Units=mm Mechanical tolerance=+/-0.2mm Die positioning tolerance=+/-0.030mm

